



- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

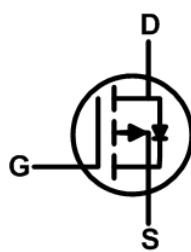
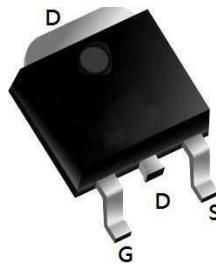
BVDSS	RDS(ON)	ID
-20V	12mΩ	-40A

Description

The XXW40P02 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XXW40P02 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252 Pin Configuration



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	-40	A
	$T_A = 100^\circ\text{C}$		-15.7	
Pulsed Drain Current ¹		I_{DM}	-66	A
Single Pulse Avalanche Energy ²		EAS	28.8	mJ
Total Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	30	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	$R_{\theta JA}$	41.6	°C/W

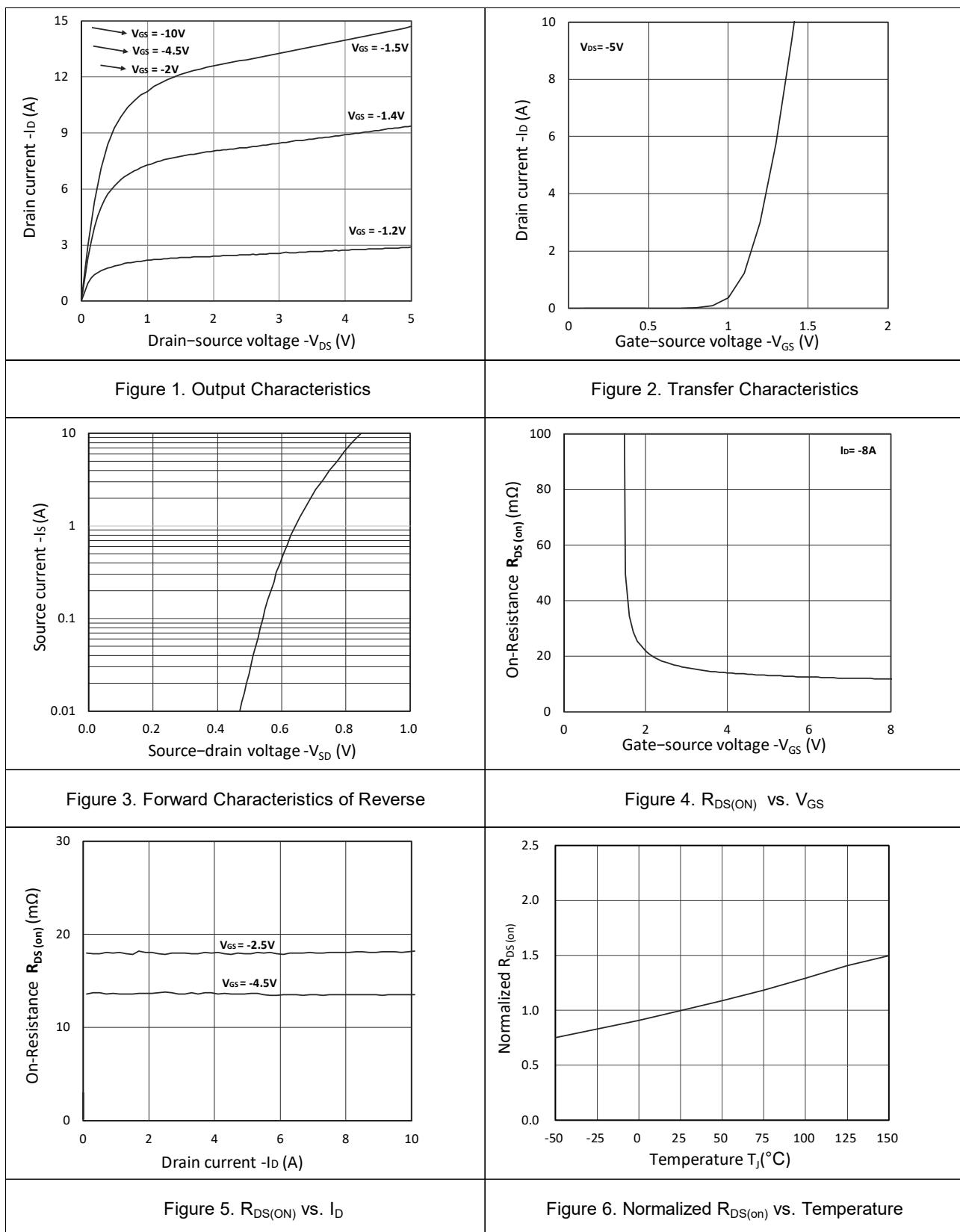
Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

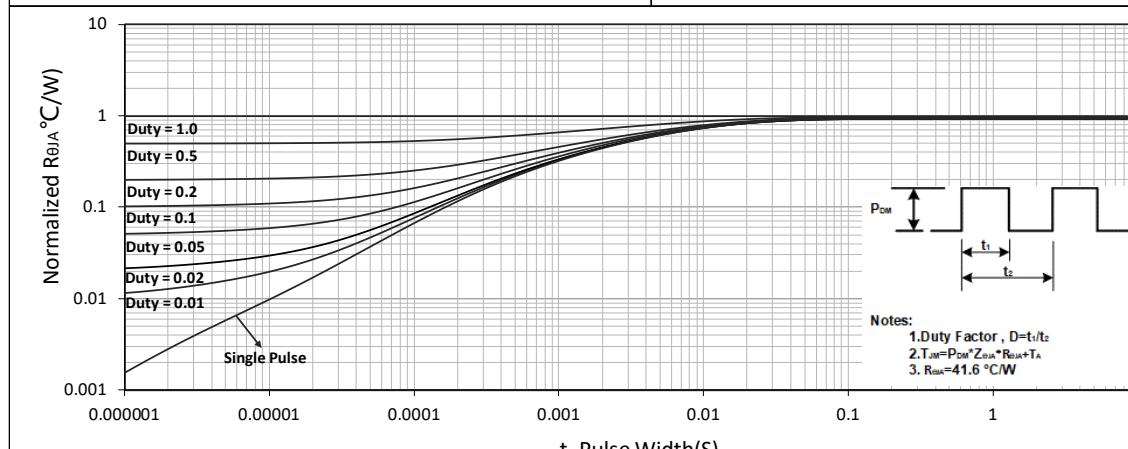
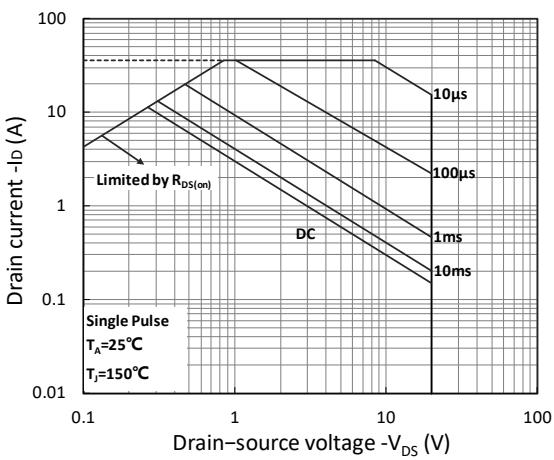
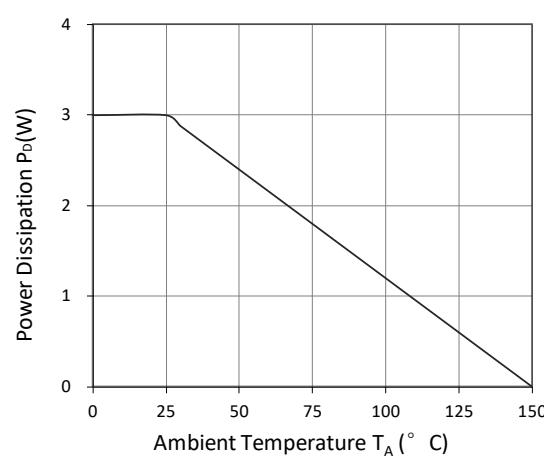
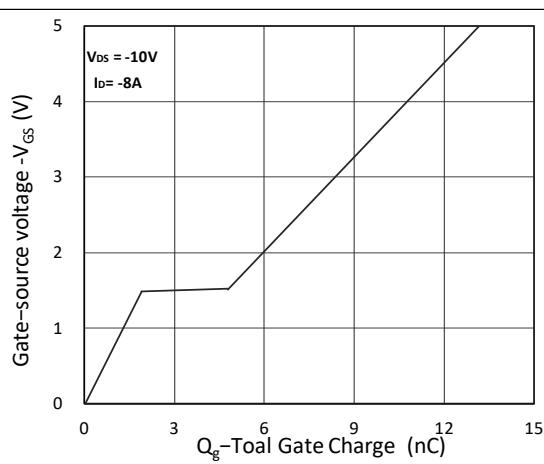
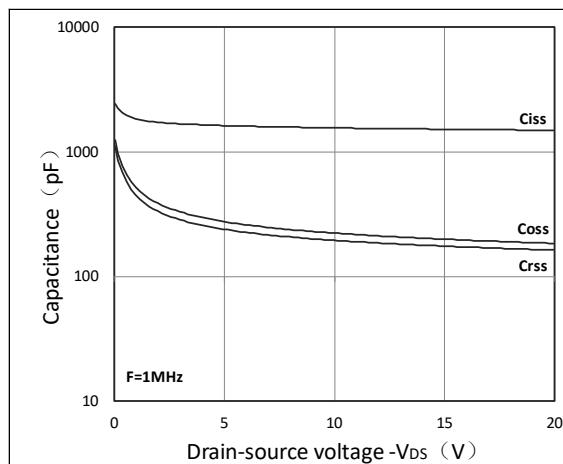
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$	-20	-	-	V
Gate-body Leakage current	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 12\text{V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current $T_J = 25^\circ\text{C}$ $T_J = 100^\circ\text{C}$	I_{DSS}	$V_{\text{DS}} = -20\text{V}, V_{\text{GS}} = 0\text{V}$	-	-	-1	μA
			-	-	-100	
Gate-Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -250\mu\text{A}$	-0.4	-0.65	-1	V
Drain-Source On-Resistance ⁴	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -4.5\text{V}, I_D = -8\text{A}$	-	12.0	18	$\text{m}\Omega$
		$V_{\text{GS}} = -2.5\text{V}, I_D = -6\text{A}$	-	17	23	
Forward Transconductance ⁴	g_{fs}	$V_{\text{DS}} = -4.5\text{V}, I_D = -8\text{A}$	-	36	-	S
Dynamic Characteristics⁵						
Input Capacitance	C_{iss}	$V_{\text{DS}} = -10\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$	-	1630	-	pF
Output Capacitance	C_{oss}		-	211	-	
Reverse Transfer Capacitance	C_{rss}		-	187	-	
Gate Resistance	R_g	$f = 1\text{MHz}$	-	10	-	Ω
Switching Characteristics⁵						
Total Gate Charge	Q_g	$V_{\text{GS}} = -4.5\text{V}, V_{\text{DS}} = -10\text{V}, I_D = -8\text{A}$	-	12	-	nC
Gate-Source Charge	Q_{gs}		-	1.8	-	
Gate-Drain Charge	Q_{gd}		-	3.2	-	
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{\text{GS}} = -4.5\text{V}, V_{\text{DD}} = -10\text{V}, R_G = 3\Omega, I_D = -8\text{A}$	-	17	-	ns
Rise Time	t_r		-	25.5	-	
Turn-Off Delay Time	$t_{d(\text{off})}$		-	32	-	
Fall Time	t_f		-	15	-	
Drain-Source Body Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$I_S = -8\text{A}, V_{\text{GS}} = 0\text{V}$	-	-	-1.2	V
Continuous Source Current $T_A = 25^\circ\text{C}$	I_S	-	-	-	-40	A

Notes:

- Repetitive rating, pulse width limited by junction temperature $T_{J(\text{MAX})}=150^\circ\text{C}$.
- The EAS data shows Max. rating . The test condition is $V_{\text{DD}}= -25\text{V}, V_{\text{GS}}= -10\text{V}, L= 0.1\text{mH}, I_{\text{AS}}= -24\text{A}$
- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
- The data tested by pulsed , pulse width $\leq 300\text{us}$, duty cycle $\leq 2\%$.
- This value is guaranteed by design hence it is not included in the production test..

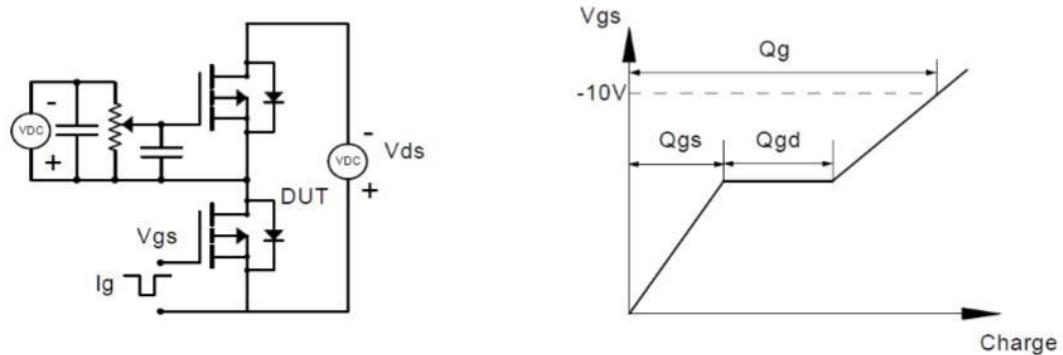
Typical Characteristics



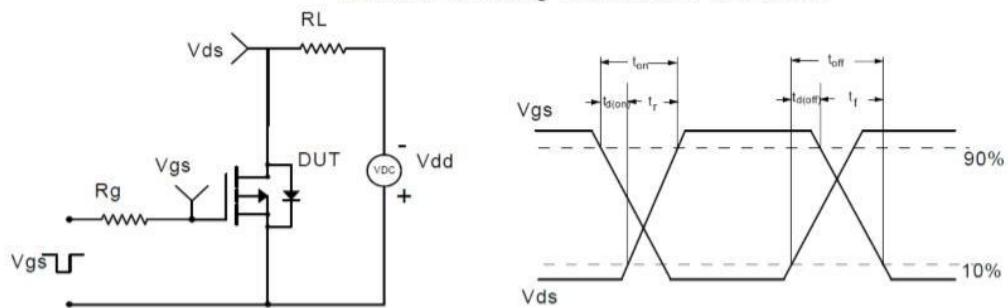


Test Circuit

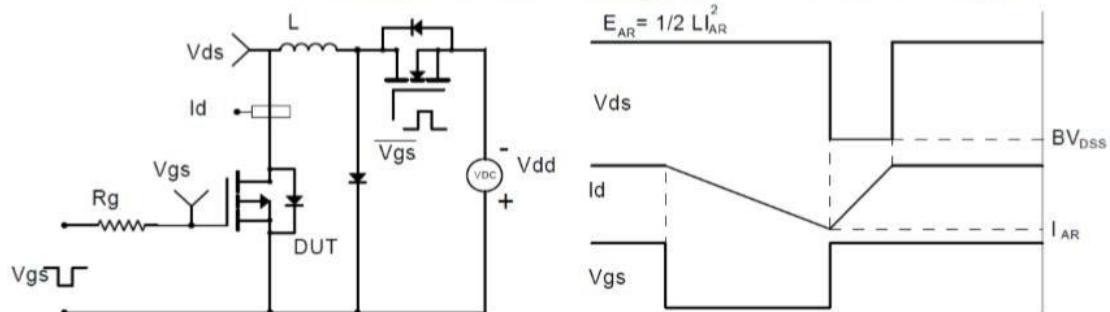
Gate Charge Test Circuit & Waveform



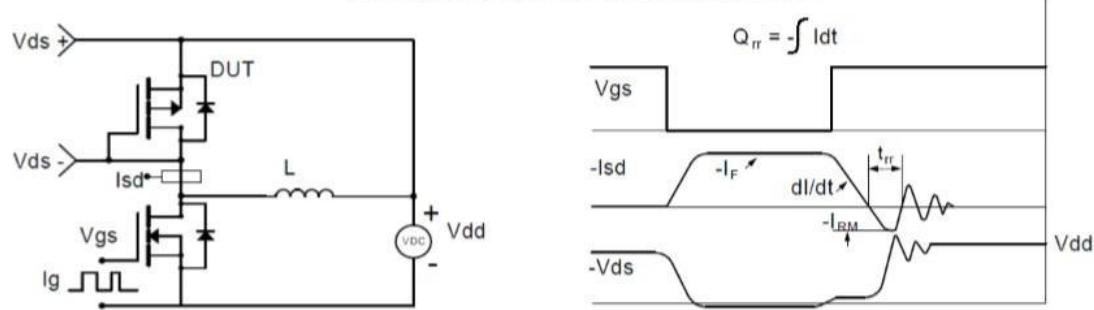
Resistive Switching Test Circuit & Waveforms



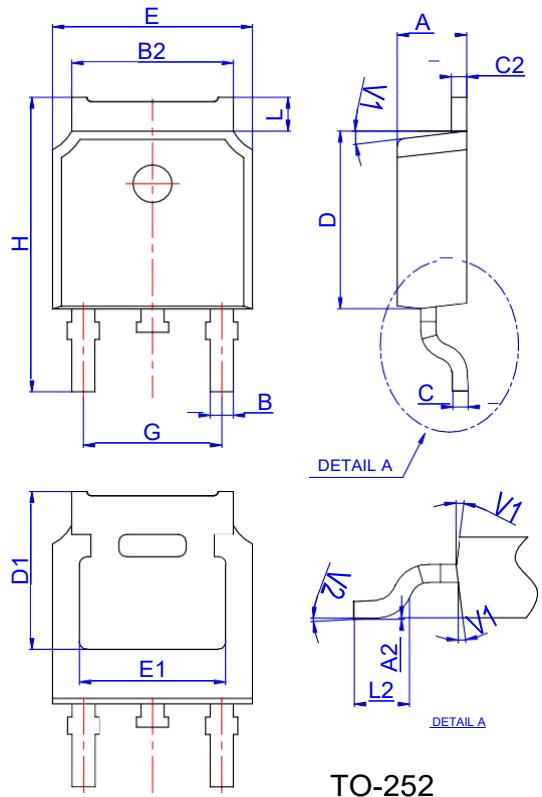
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

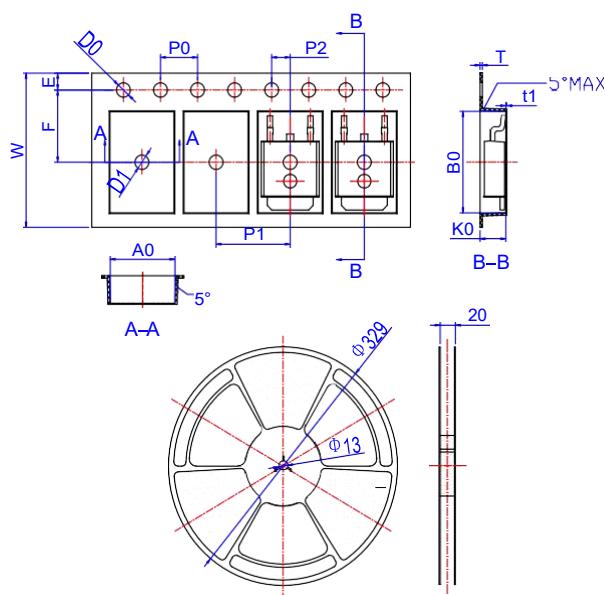


Package Mechanical Data TO 252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252-4R



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583